

# Deposition Rates on PVD75 DC/RF Magnetron Sputterer (Graduate Student Fellow Program)

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## SiO<sub>2</sub>

- Base Pressure: less than  $5 \times 10^{-7}$  Torr
- Process Ar Pressure: 3 mTorr
- RF Power:
- Deposition Rate:  $1.2 \pm 0.2$  nm/min
- Thickness measurement: P7 stylus profiler

## Ni

- Base Pressure: less than  $5 \times 10^{-7}$  Torr
- Process Ar Pressure: 3 mTorr
- DC Power: 400 W
- Deposition Rate:  $21.1 \pm 1.1$  nm/min
- Thickness measurement: P7 stylus profiler

## Al

- Base Pressure: less than  $5 \times 10^{-7}$  Torr
- Process Ar Pressure: 3 mTorr
- DC Power: 400 W
- Deposition Rate:  $11.0 \pm 2.1$  nm/min
- Thickness measurement: P7 stylus profiler

### Al Deposition

